Driver Transistors

PNP Silicon

Features

- AEC-Q101 Qualified and PPAP Capable
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage MMBTA55 MMBTA56, SMMBTA56	V _{CEO}	-60 -80	Vdc
Collector - Base Voltage MMBTA55 MMBTA56, SMMBTA56	V _{CBO}	-60 -80	Vdc
Emitter - Base Voltage	V _{EBO}	-4.0	Vdc
Collector Current - Continuous	I _C	-500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = 0.4 \times 0.3 \times 0.024 in. 99.5% alumina.

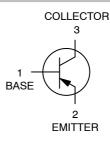


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SOT-23 CASE 318 STYLE 6



MARKING DIAGRAM



2xx = Device Code x = H for MMBTA55LT1G xx = GM for MMBTA56LT1G, SMMBTA56LT1G

M = Date Code*= Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

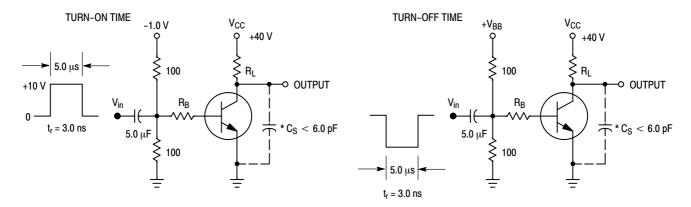
See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	<u> </u>			
Collector – Emitter Breakdown Voltage (Note 3) (I _C = -1.0 mAdc, I _B = 0) MMBTA55 MMBTA56, SMMBTA56	V _(BR) CEO	-60 -80	- -	Vdc
Emitter – Base Breakdown Voltage (I _E = -100 μAdc, I _C = 0)	V _{(BR)EBO}	-4.0	-	Vdc
Collector Cutoff Current (V _{CE} = -60 Vdc, I _B = 0)	I _{CES}	-	-0.1	μAdc
Collector Cutoff Current	Ісво	-	-0.1 -0.1	μAdc
ON CHARACTERISTICS	,			
DC Current Gain $ \begin{pmatrix} I_C = -10 \text{ mAdc, } V_{CE} = -1.0 \text{ Vdc} \end{pmatrix} $ $ \begin{pmatrix} I_C = -100 \text{ mAdc, } V_{CE} = -1.0 \text{ Vdc} \end{pmatrix} $	h _{FE}	100 100	- -	-
Collector – Emitter Saturation Voltage (I _C = -100 mAdc, I _B = -10 mAdc)	V _{CE(sat)}	_	-0.25	Vdc
Base – Emitter On Voltage (I _C = -100 mAdc, V _{CE} = -1.0 Vdc)	V _{BE(on)}	_	-1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS	, ,		•	•
Current – Gain – Bandwidth Product (Note 4) $(I_C = -100 \text{ mAdc}, V_{CE} = -1.0 \text{ Vdc}, f = 100 \text{ MHz})$	f _T	50	-	MHz

^{3.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%. 4. f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.



^{*}Total Shunt Capacitance of Test Jig and Connectors For PNP Test Circuits, Reverse All Voltage Polarities

Figure 1. Switching Time Test Circuits

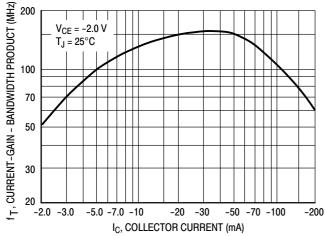


Figure 2. Current-Gain — Bandwidth Product

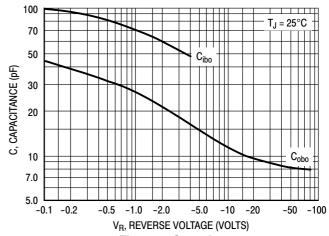


Figure 3. Capacitance

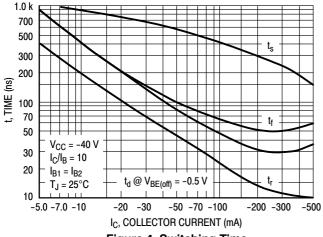


Figure 4. Switching Time

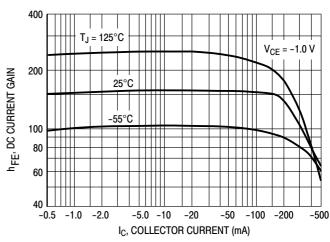


Figure 5. DC Current Gain

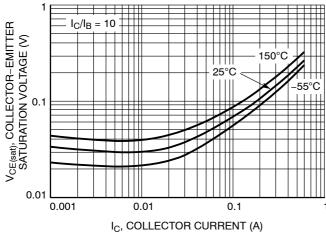


Figure 6. Collector Emitter Saturation Voltage vs. Collector Current

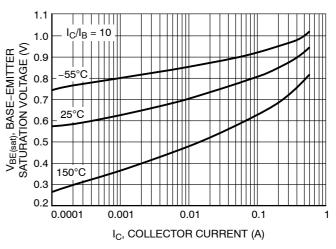


Figure 7. Base Emitter Saturation Voltage vs.
Collector Current

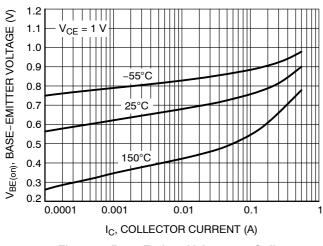


Figure 8. Base Emitter Voltage vs. Collector Current

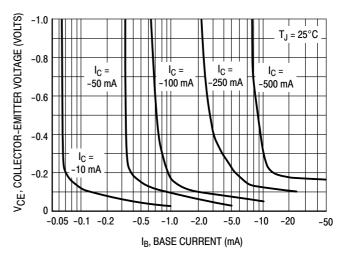


Figure 9. Collector Saturation Region

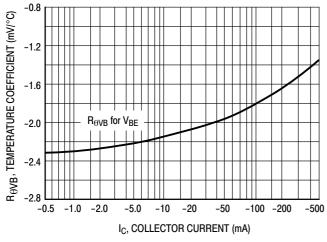


Figure 10. Base–Emitter Temperature Coefficient

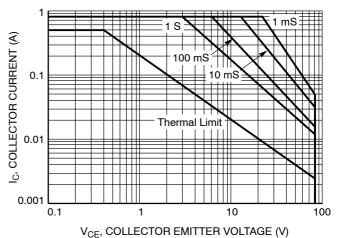


Figure 11. Safe Operating Area

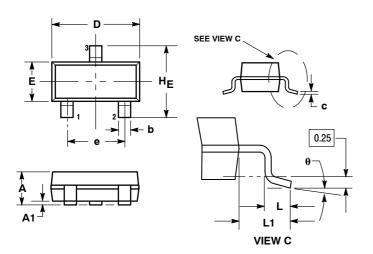
ORDERING INFORMATION

Device Order Number	Package Type	Shipping [†]	
MMBTA55LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel	
MMBTA55LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel	
MMBTA56LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel	
SMMBTA56LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel	
MMBTA56LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel	
SMMBTA56LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel	

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AP**



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH
 THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,
- PROTRUSIONS, OR GATE BURRS.

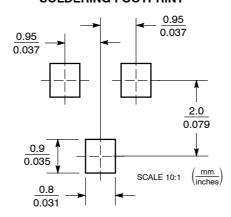
	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
С	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104
A	٥°		10°	٥°		10°

STYLE 6:

PIN 1. BASE

- **EMITTER**
- COLLECTOR

SOLDERING FOOTPRINT



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